

N-Channel Enhancement Mode Power MOSFET

Description

The HM4484 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

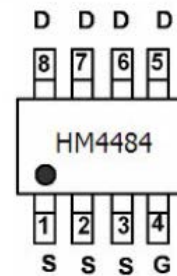
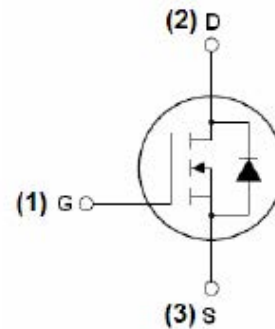
- $V_{DS} = 40V, I_D = 15A$
 $R_{DS(ON)} < 13m\Omega @ V_{GS} = 10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔV_d s TESTED!



Marking and pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4484	HM4484	SOP8	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	15	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	10	A
Pulsed Drain Current	I_{DM}	50	A
Maximum Power Dissipation	P_D	$\dot{A}l$	$\dot{A}V$
Derating factor		0.43	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	400	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.3	$^{\circ}C/W$
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Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	45	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	7.3	13	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=FI A$	15	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	1800	-	PF
Output Capacitance	C_{oss}		-	280	-	PF
Reverse Transfer Capacitance	C_{rss}		-	190	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=2A, R_L=1\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	6.4	-	nS
Turn-on Rise Time	t_r		-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29.6	-	nS
Turn-Off Fall Time	t_f		-	16.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=FI A,$ $V_{GS}=10V$	-	29	-	nC
Gate-Source Charge	Q_{gs}		-	4.5	-	nC
Gate-Drain Charge	Q_{gd}		-	6.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	15	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = FI A$ $di/dt = 100A/\mu s$ ^(Note3)	-	29	-	nS
Reverse Recovery Charge	Q_{rr}		-	26	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

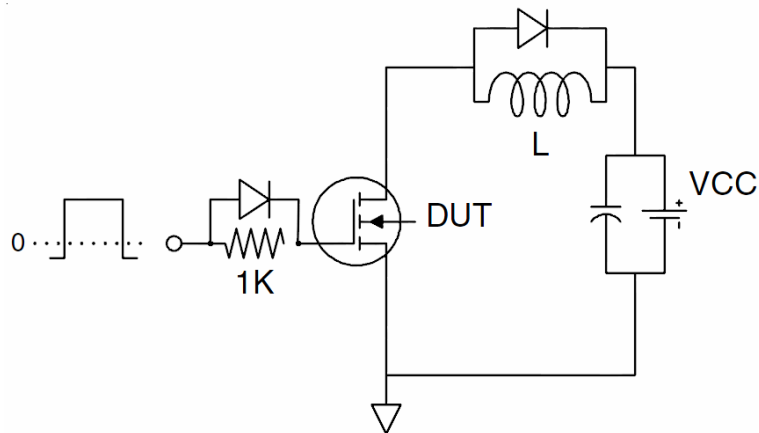
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega,$

Test circuit

1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

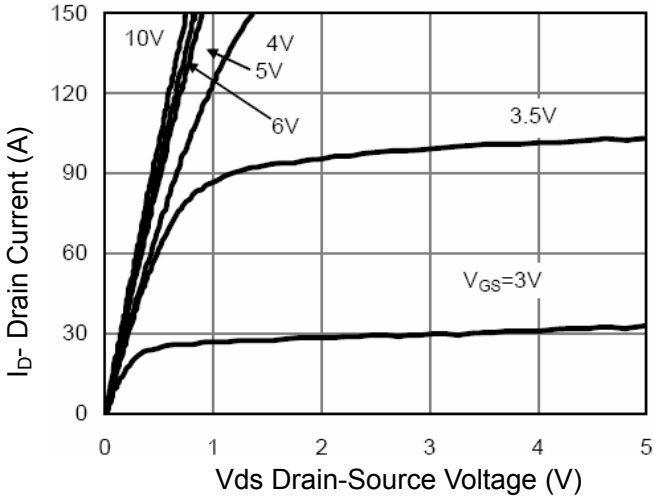


Figure 1 Output Characteristics

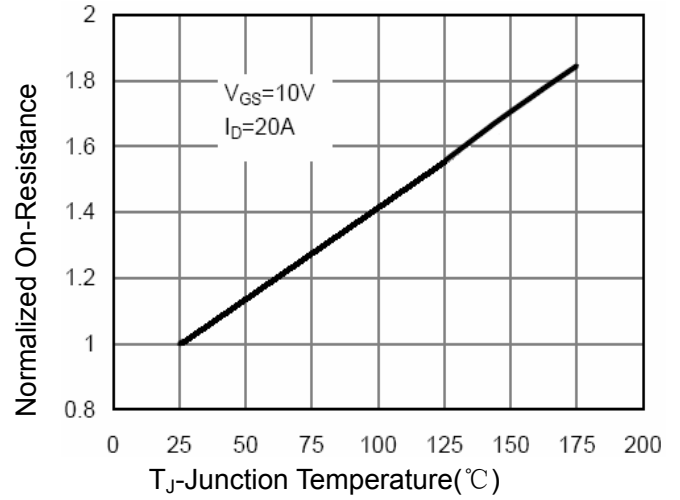


Figure 4 Rds(on)-Junction Temperature

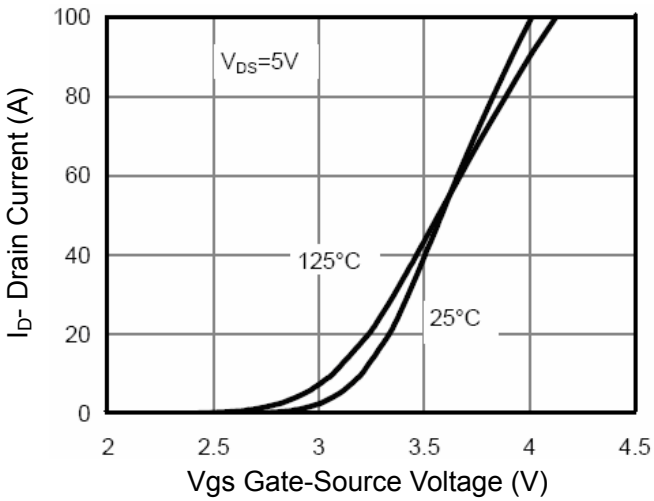


Figure 2 Transfer Characteristics

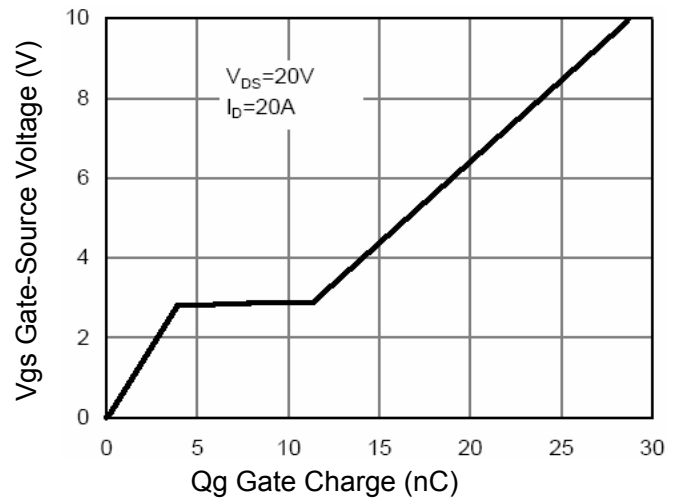


Figure 5 Gate Charge

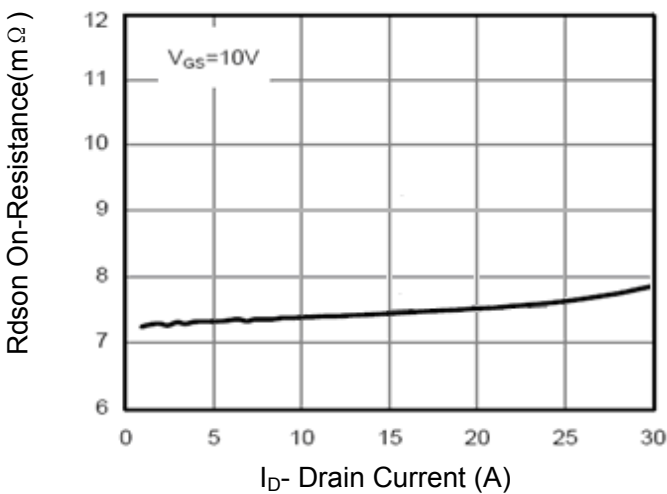


Figure 3 Rds(on)- Drain Current

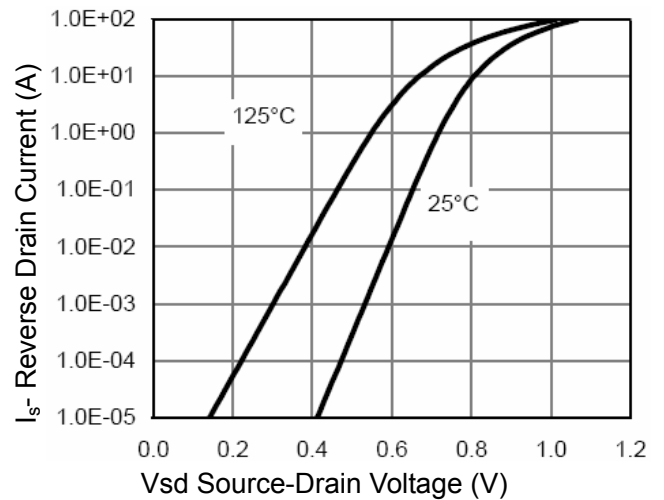


Figure 6 Source- Drain Diode Forward

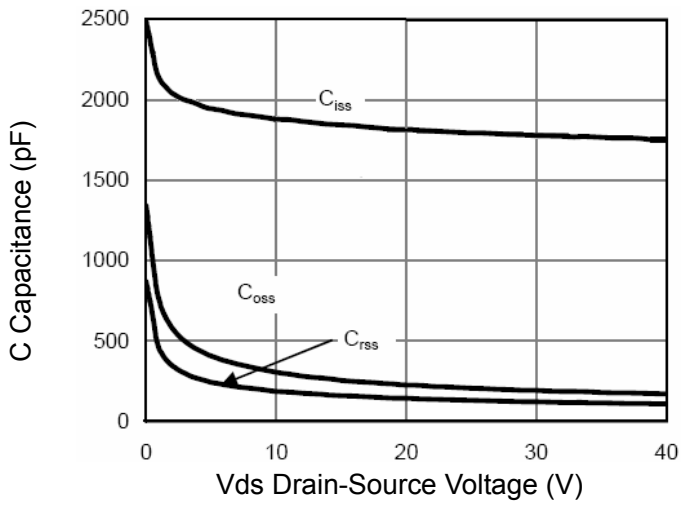


Figure 7 Capacitance vs Vds

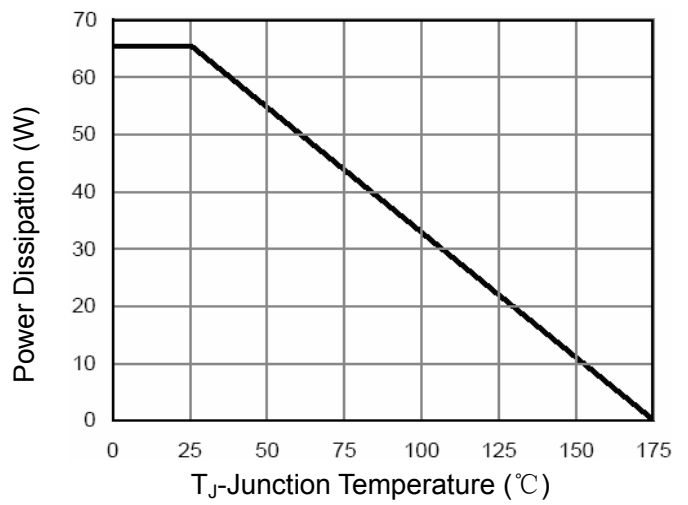


Figure 9 Power De-rating

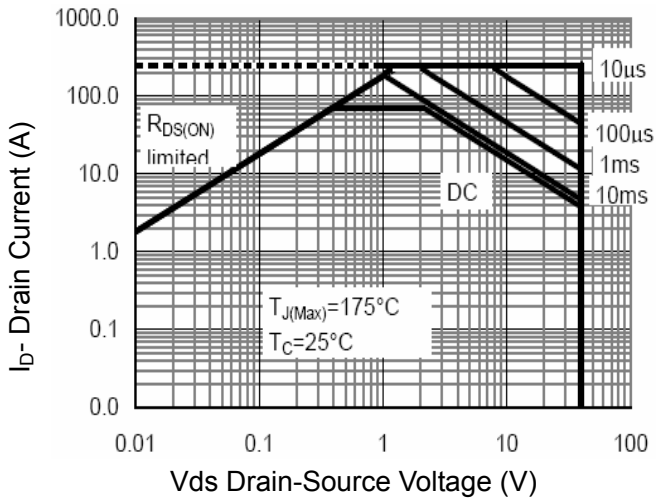


Figure 8 Safe Operation Area

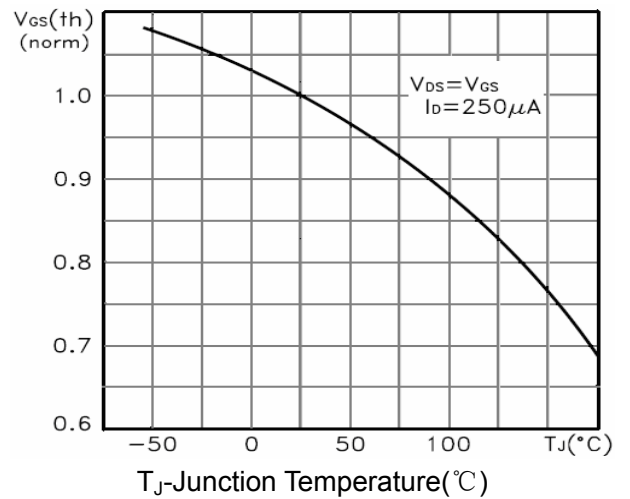


Figure 10 $V_{GS(th)}$ vs Junction Temperature

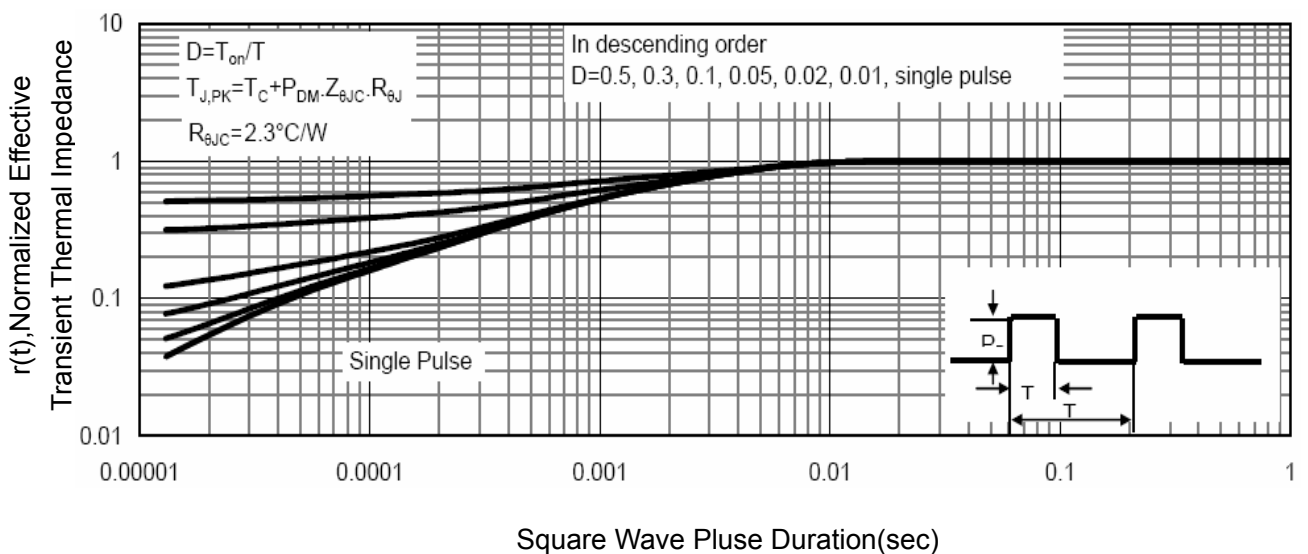
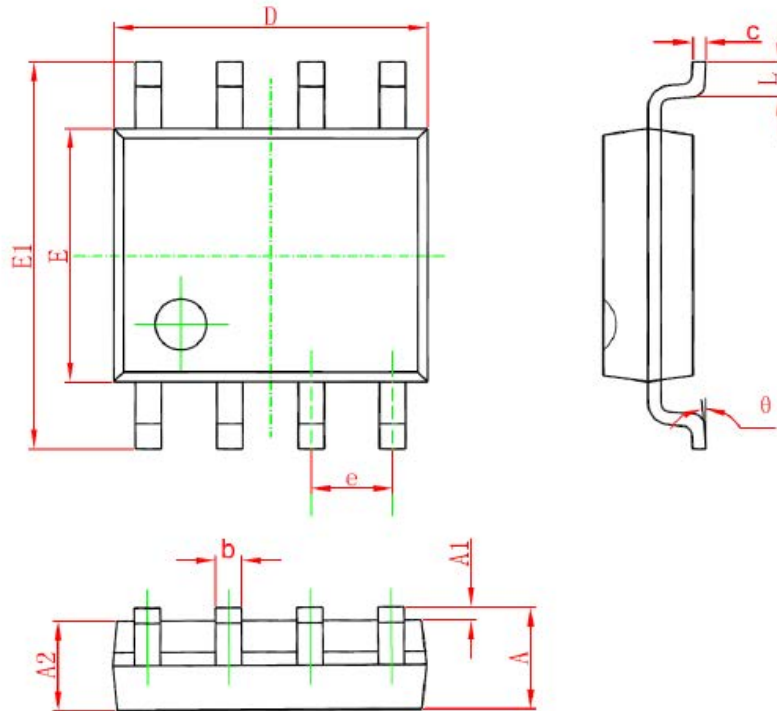


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	